Monolithic linear IC

# LA5621M, 5621V

## Lithium-Ion Battery Charge Control IC

### **Overview**

The LA5621M and LA5621V are external charge control ICs for lithium-ion batteries. These ICs are ideally suited for on/off control of external power MOSFETs in systems that incorporate a charging circuit in the set. They detect the charge and discharge status, output it to the set control microcontroller, which then outputs a signal to switch external power MOSFETS either on or off. Moreover, these ICs have a built-in function that detects discharge (countercurrent) from lithium-ion batteries within sets to external lithium-ion batteries in an AC adapter/charger, etc. and switches external power MOSFETs off.

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### Application

• Charge control of 1- or 2-cell lithium-ion batteries of video cameras, digital still cameras, cellular telephones, etc., used in combination with a microcontroller.

### Functions

- Charge/discharge: In charge/discharge mode, switch external power MOSFETs on to charge the battery or discharge it to set load.
- Charge detection: Detect the charge status of lithium-ion batteries with comparator.
- Charge completion control: When charging of the lithium-ion battery is completed, the comparator is activated and the external power MOSFETs are switched off to stop charging.

- Countercurrent detection and control:
- In systems that support charging of both the set of the video camera, etc., and the AC adapter/charger, when spare batteries are charged on the AC adapter/charger side, if the battery voltage on the set side becomes high when the set is connected to the AC adapter/charger, current flows out to the battery on the AC adapter/charger side. These ICs feature a function that prevents this from happening.
- Charge prevention: A specified voltage is applied to the CHARGEINH pin to stop charging.

### **Features**

- The combination of a microcontroller and external power MOSFETs enables easy charge/discharge control of lithium-ion batteries.
- Small power dissipation makes these ICs suitable for sets that require long time operation
- Use of compact package makes these ICs suitable for compact sets.
- Large power supply operation range supports both 1-cell and 2-cell lithium-ion batteries.

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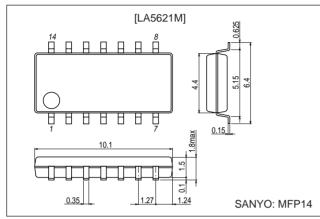
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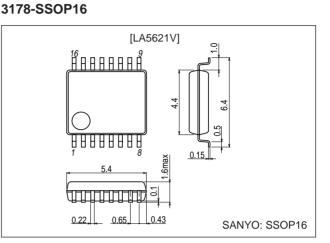
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# **Package Dimensions**

unit: mm

### 3034A-MFP14





# Specifications

Maximum Rating at  $Ta=25^{\circ}C$ 

Parameter Symbol		Conditions	Ratings	Unit
Maximum supply voltage V <sub>CC</sub> max			11	V
Allowable neuron discipation	Pd max	LA5621M	320	mW
Allowable power dissipation		LA5621V	250	mW
Operating temperature Topr			-20 to +75	°C
Storage temperature Tstg			-55 to +125	°C

### Allowable Operating Conditions at $Ta=25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage 1	V <sub>CC</sub> 1	$V_{CC}1 \le V_{CC}2$	1 to 11	V
Supply voltage 2	V <sub>CC</sub> 2	$V_{CC}1 \leq V_{CC}2*$	2 to 5.5	V

Note: \* When  $V_{CC} 1 < 2$  V, only the gate block (external power MOSFET drive) operates.

## Electrical Characteristics at Ta = $25^{\circ}$ C, V<sub>CC</sub>1 = 5.5 V, V<sub>CC</sub>2 = 3.15 V (unless otherwise specified)

Deverselan	Ourseland.	F		Ratings	Ratings			
Parameter	Symbol	Conditions	min	typ	max	Unit		
Current drain 1-1 (During set operation discharge)	I <sub>CC</sub> 1-1	$V_{CC}$ 1 in current, $V_{CHG} = V_{CC}$ 2, SW4, 6: on, SW5: off		90	120	μA		
Current drain 2-1 (During set operation discharge)	I <sub>CC</sub> 2-1	$V_{CC}$ 2 in current, $V_{CHG} = V_{CC}$ 2, SW4, 6: on, SW5: off		20	26	μA		
Current drain 1-2 (During charging outside set)	I <sub>CC</sub> 1-2	$V_{CC}$ 2 in current, $V_{CHG} = V_{CC}$ 2, SW4, 5: on		20	26	μA		
Current drain 2-2 (During charging)	I <sub>CC</sub> 2-2	V <sub>CC</sub> 2 in current SW5: on, V <sub>CPU</sub> : L, V <sub>GATE</sub> :H		600	800	μA		
[Output pin block]	[Output pin block]							
High-level CPU pin	V <sub>CPU-H</sub>	$V_{IN}1^- = 15 \text{ mV}, V_{IN}1^+ = 11 \text{ mV},$ $V_{CHG} = V_{CC}2$ , SW4: off, SW5: on	V <sub>CC</sub> 2-0.15			V		
Low-level CPU pin	V <sub>CPU-L</sub>	$V_{IN}1^-$ = 15 mV, $V_{IN}1^+$ = 23 mV, $V_{CHG}$ = $V_{CC}2$ , SW4: off, SW5: on			0.2	V		
CPU pin sink current	V <sub>CPU-SINK</sub>	$V_{IN}1^- = 15 \text{ mV}, V_{IN}1^+ = 23 \text{ mV},$ $V_{CHG} = V_{CC}2$ , SW4: off, SW5: on		35		μA		
High-level BIAS1 pin	V <sub>BIAS</sub> 1-H	SW1, 2, 5, 6: on	V <sub>CC</sub> 2-0.15			V		
High-level BIAS2 pin	V <sub>BIAS</sub> 2-H	SW1, 2, 5, 6: on, $V_{IN}2^-$ = 15 mV, $V_{IN}2^+$ = 11 mV	V <sub>CC</sub> 2-0.15			V		
Low-level BIAS2 pin leak current	I <sub>BIAS</sub> 2-LK	SW1, 2, 5, 6: on, V <sub>IN</sub> 1 <sup>-</sup> = 15 mV, V <sub>IN</sub> 1 <sup>+</sup> = 23 mV			10	μA		

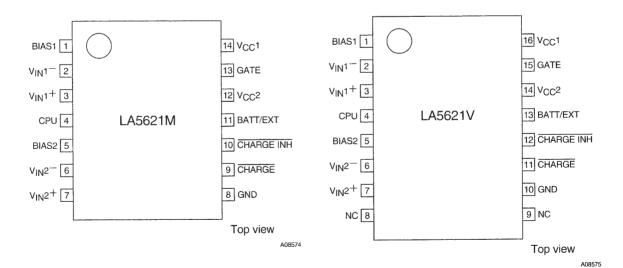
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Deservator	O week at	Quandité	Ratings			
Parameter	Symbol Conditions		min	typ	max	Unit
[FET drive block]						
Drive high-level voltage	V <sub>GATE-H</sub>	Same as current drain 1-1	5.3	5.4		V
Drive low-level voltage	V <sub>GATE-L</sub>	SW6: on, Same as current drain 1-2		0.1	0.2	V
[Comparator block] SW1, 2, 5, 6: on						-
Input offset voltage 1	V <sub>IO</sub> 1	Comparator 1, when CPU voltage is reversed	-3	+2	+7	mV
Input offset voltage 2	V <sub>IO</sub> 2	Comparator 2, when BIAS2 voltage is reversed	-3	-1	+1	mV
Input offset voltage 3	V <sub>IO</sub> 3	Total temperature, comparator 2	-5		+3	mV
Input offset current	I <sub>IO</sub>	Comparators 1, 2		5	50	nA
Input bias current	I <sub>IB</sub>	Comparators 1, 2	-250	-25		nA
In-phase input voltage range	VICR	Comparators 1, 2			V <sub>CC</sub> 2 – 1.5	V
Input current during negative voltage application	I <sub>LIM</sub>	Comparators 1, 2 non-reversed input block only, SW3: on	-1.5			mA
[Input pin block] $V_{IN}1^- = 15 \text{ mV}, V_{IN}1^+ = 23 \text{ mV}$	, V <sub>IN</sub> 2- = 15	mV, V <sub>IN</sub> 2+ = 23 mV				
CHARGE pin threshold voltage	V <sub>CHG-TH</sub>	SW1, 2, 5, 6: When on, BIAS2 voltages are reversed	0.5		1.2	V
CHARGE pin input bias current 1	I <sub>CHG-BI</sub> 1	Current during threshold voltage			10	μA
CHARGE pin input bias current 2	I <sub>CHG-BI</sub> 2	$V_{\overline{CHARGE}} = V_{CC}2$	55	70	85	μA
CHARGE-INH pin open voltage	V <sub>CH-IN-OP</sub>	SW1, 2, 5, 6: on		V <sub>CC</sub> 2		V
CHARGE-INH pin threshold voltage	V <sub>CH-IN-TH</sub>	SW1, 2, 5, 6: When on, BIAS2 voltages are reversed	0.7		1.3	V
CHARGE-INH pin low-level input current	I <sub>CH-IN</sub>	SW1, 2, 5, 6: on	-30			μA
BATT/EXT pin open voltage	V <sub>BA/EX-OP</sub>	SW1, 2, 6: on		V <sub>CC</sub> 2		V
BATT/EXT pin threshold voltage	V <sub>BA/EX-TH</sub>	SW1, 2, 6: When on, BIAS2 voltages are reversed	1.45		2.05	V
BATT/EXT pin low-level input current	V <sub>BA/EX</sub>	SW1, 2, 5, 6: on	-30			μA

Handling Cautions

Observe precautions when handling these ICs because they are electrostatic sensitive devices.

### **Pin Assignment**



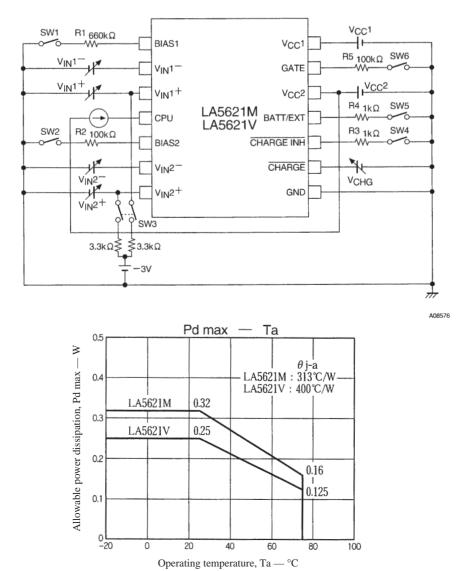
#### LA5621M, 5621V

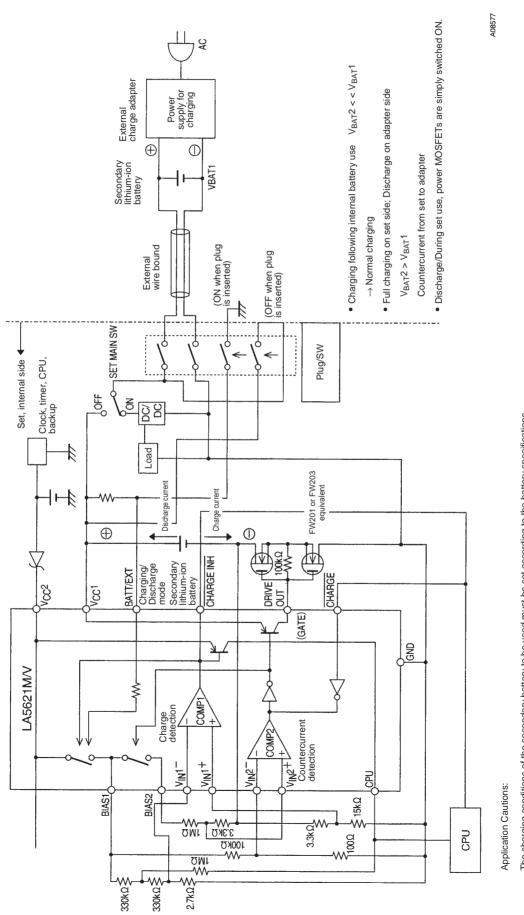
#### **Pin Functions**

Pin No.		Dia nomo	Function		
LA5621M	LA5621V	- Pin name	Function		
1	1	BIAS1	Resistor connection pin for setting non-reversed input potential of comparator 1		
2	2	V <sub>IN</sub> 1-*	Reversed input of comparator 1 (for charge current detection)		
3	3	V <sub>IN</sub> 1+*	Non-reversed input of comparator 1 (for charge current detection)		
4	4	CPU	Microcontroller signal input pin		
5	5	BIAS2	Resistor connection pin for setting non-reversed input potential of comparator 2		
6	6	V <sub>IN</sub> 2-*	Reversed input of comparator 2 (for countercurrent detection when 2 batteries are used)		
7	7	V <sub>IN</sub> 2+*	Non-reversed input of comparator 2 (for countercurrent detection when 2 batteries are used)		
—	8	NC	No connection		
_	9	NC	No connection		
8	10	GND	Substrate of this IC (Lowest potential)		
9	11	CHARGE	Charging signal input pin, charge with low		
10	12	CHARGE INH	Charge prohibition signal input pin, charge prohibition with low (becomes low during discharge mode for lithium-ion battery that set operates on)		
11	13	BATT/EXT	On/off control pin of this IC, except Gate block (becomes "Open" during discharge mode for lithium-ion battery that set operates on)		
12	14	V <sub>CC</sub> 2	Power supply input		
13	15	GATE	Gate connection pin of external power MOSFETs		
14	16	V <sub>CC</sub> 1	Lithium-ion battery + side input pin		

Note: \* If negative voltage is applied due to countercurrent, etc., up to 1.5 mA can be allowed.

### **Specified Test Circuit**







The charging conditions of the secondary battery to be used must be set according to the battery specifications. The peripheral circuit constants must be set taking into consideration the specifications of the power MOSFETs. Microcontroller use conditions must be carefully studied.

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